

## PSMN1R5-40ES

# N-channel 40 V 1.6 m $\Omega$ standard level MOSFET in I2PAK. Rev. 01 — 19 April 2011 Product data

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Standard level N-channel MOSFET in I2PAK (SOT226) package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC convertors
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                        | Conditions   |     | Min | Тур | Max | Unit |
|-------------------------|----------------------------------|--|-----|-----|-----|-----|------|
| $V_{DS}$                | drain-source voltage             | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$  |     | -   | -   | 40  | V    |
| I <sub>D</sub>          | drain current                    | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V;<br>see <u>Figure 1</u>  | [1] | -   | -   | 120 | Α    |
| P <sub>tot</sub>        | total power dissipation          | T <sub>mb</sub> = 25 °C; see Figure 2  |     | -   | -   | 338 | W    |
| Static characteristics  |                                  |  |     |     |     |     |      |
| R <sub>DSon</sub>       | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$ | [2] | -   | 1.3 | 1.6 | mΩ   |
| Dynamic characteristics |                                  |  |     |     |     |     |      |
| $Q_{GD}$                | gate-drain charge                | $V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$   |     | -   | 32  | -   | nC   |
| Q <sub>G(tot)</sub>     | total gate charge                | V <sub>DS</sub> = 20 V; see <u>Figure 14;</u><br>see <u>Figure 15</u>  |     | -   | 136 | -   | nC   |

<sup>[1]</sup> Continuous current is limited by package



<sup>[2]</sup> Measured 3 mm from package.

### 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol        |
|-----|--------|-------------|--------------------|-----------------------|
| 1   | G      | gate        |                    | _                     |
| 2   | D      | drain       | mb                 | D                     |
| 3   | S      | source      |                    | $G \longrightarrow X$ |
| mb  | D      | drain       |                    | mbb076 S              |
|     |        |             |                    |                       |
|     |        |             | SOT226 (I2PAK)     |                       |

### 3. Ordering information

Table 3. Ordering information

| Type number  | Package |  |         |
|--------------|---------|--|---------|
|              | Name    | Description                                  | Version |
| PSMN1R5-40ES | I2PAK   | plastic single-ended package (I2PAK); TO-262 | SOT226  |

### 4. Limiting values

Table 4. Limiting values

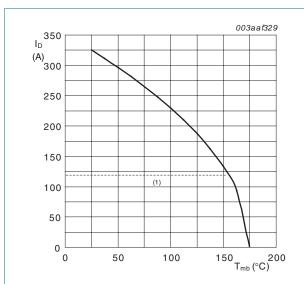
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                    | Conditions  |     | Min | Max  | Unit |
|----------------------|--|---|-----|-----|------|------|
| $V_{DS}$             | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C   |     | -   | 40   | V    |
| $V_{DGR}$            | drain-gate voltage                           | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$  |     | -   | 40   | V    |
| $V_{GS}$             | gate-source voltage                          |   |     | -20 | 20   | V    |
| $I_D$                | drain current                                | $V_{GS} = 10 \text{ V}; T_{mb} = 100 ^{\circ}\text{C}$  | [1] | -   | 120  | Α    |
|                      |  | $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$                  | [1] | -   | 120  | Α    |
| I <sub>DM</sub>      | peak drain current                           | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3  |     | -   | 1301 | Α    |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>  |     | -   | 338  | W    |
| T <sub>stg</sub>     | storage temperature                          |   |     | -55 | 175  | °C   |
| Tj                   | junction temperature                         |   |     | -55 | 175  | °C   |
| T <sub>sld(M)</sub>  | peak soldering temperature                   |   |     | -   | 260  | °C   |
| Source-drain         | n diode                                      |   |     |     |      |      |
| Is                   | source current                               | T <sub>mb</sub> = 25 °C   | [1] | -   | 120  | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$  |     | -   | 1301 | Α    |
| Avalanche r          | uggedness                                    |   |     |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 40 V; unclamped; $R_{GS}$ = 50 Ω; $t_p$ = 0.1 ms |     | -   | 1.4  | J    |

[1] Continuous current is limited by package.

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 $V_{\it GS} \geq$  10 V(1) Capped at 120 A due to package

Fig 1. Normalized continuous drain current as a function of mounting base temperature

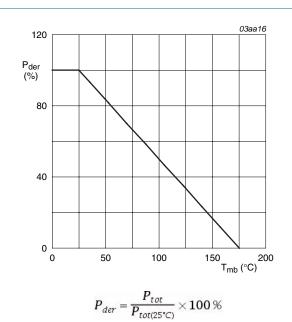
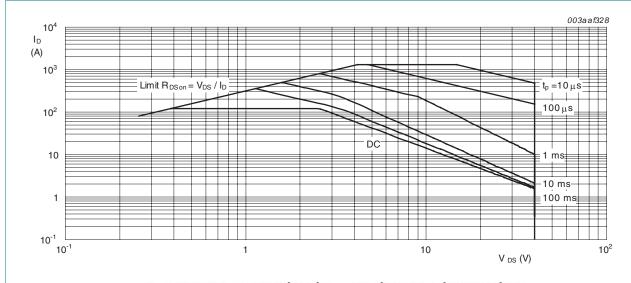


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse; Capped at 120 A due to package

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol               | Parameter   | Conditions           | Min | Тур  | Max  | Unit |
|----------------------|---|----------------------|-----|------|------|------|
| $R_{th(j-mb)}$       | thermal resistance from junction to mounting base | see Figure 4         | -   | 0.22 | 0.44 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient       | Vertical in free air | -   | 60   | -    | K/W  |

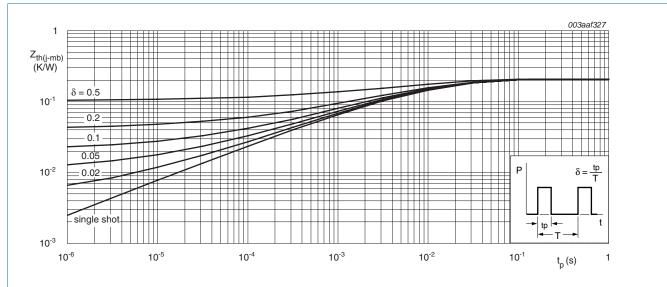


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 6. Characteristics

Table 6. Characteristics

| Symbol                 | Parameter                         | Conditions  | Min  | Тур  | Max   | Unit |
|------------------------|-----------------------------------|---|------|------|-------|------|
| Static cha             | racteristics                      |   |      |      |       |      |
| V <sub>(BR)DSS</sub>   | drain-source breakdown            | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$   | 36   | -    | -     | V    |
|                        | voltage                           | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$  | 40   | -    | -     | V    |
| $V_{GS(th)}$           | gate-source threshold voltage     | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 10                                       | -    | -    | 4.6   | V    |
|                        |                                   | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 10                                       | 1    | -    | -     | V    |
|                        |                                   | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 11; see Figure 10                         | 2    | 3    | 4     | V    |
| I <sub>DSS</sub>       | drain leakage current             | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                    | -    | 0.02 | 10    | μΑ   |
|                        |                                   | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$                                   | -    | 250  | 500   | μΑ   |
| I <sub>GSS</sub>       | gate leakage current              | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                    | -    | 2    | 100   | nA   |
|                        |                                   | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                   | -    | 2    | 100   | nA   |
| Doon                   | drain-source on-state resistance  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 ^{\circ}\text{C};$<br>see Figure 12             | -    | 1.9  | 2.3   | mΩ   |
|                        |                                   | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12                | -    | 2.6  | 3.2   | mΩ   |
|                        |                                   | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13                 | 1] - | 1.3  | 1.6   | mΩ   |
| R <sub>G</sub>         | internal gate resistance (AC)     | f = 1 MHz   | -    | 1.1  | -     | Ω    |
| Dynamic c              | haracteristics                    |   |      |      |       |      |
| $Q_{G(tot)}$           | total gate charge                 | $I_D = 0 \text{ A}$ ; $V_{DS} = 0 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15 | -    | 133  | -     | nC   |
|                        |                                   | $I_D = 75 \text{ A}; \ V_{DS} = 20 \text{ V}; \ V_{GS} = 10 \text{ V};$                               | -    | 136  | 136 - | nC   |
| $Q_{GS}$               | gate-source charge                | see Figure 14; see Figure 15  | -    | 52   | -     | nC   |
| Q <sub>GS(th)</sub>    | pre-threshold gate-source charge  |   | -    | 30   | -     | nC   |
| Q <sub>GS(th-pl)</sub> | post-threshold gate-source charge |   | -    | 22   | -     | nC   |
| $Q_{GD}$               | gate-drain charge                 |   | -    | 32   | -     | nC   |
| $V_{GS(pl)}$           | gate-source plateau voltage       | V <sub>DS</sub> = 20 V; see <u>Figure 14</u> ;<br>see <u>Figure 15</u>                                | -    | 6.1  | -     | V    |
| C <sub>iss</sub>       | input capacitance                 | $V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$                                     | -    | 9710 | -     | pF   |
| Coss                   | output capacitance                | T <sub>j</sub> = 25 °C; see <u>Figure 16</u>  | -    | 2042 | -     | pF   |
| C <sub>rss</sub>       | reverse transfer capacitance      |   | -    | 994  | -     | pF   |
| d(on)                  | turn-on delay time                | $V_{DS} = 20 \text{ V}; R_L = 0.8 \Omega; V_{GS} = 10 \text{ V};$                                     | -    | 45   | -     | ns   |
| r                      | rise time                         | $R_{G(ext)} = 4.7 \Omega$   | -    | 66   | -     | ns   |
| d(off)                 | turn-off delay time               |   | -    | 111  | -     | ns   |
| t <sub>f</sub>         | fall time                         |   | -    | 53   | -     | ns   |

Table 6. Characteristics ...continued

| Symbol          | Parameter             | Conditions   | Min | Тур | Max | Unit |
|-----------------|-----------------------|--|-----|-----|-----|------|
| Source-dra      | in diode              |  |     |     |     |      |
| $V_{SD}$        | source-drain voltage  | $I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17  | -   | 0.8 | 1.2 | V    |
| t <sub>rr</sub> | reverse recovery time | $I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$                         | -   | 64  | -   | ns   |
| Q <sub>r</sub>  | recovered charge      | $I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$ ; $T_j = 25 \text{ °C}$ | -   | 117 | -   | nC   |

### [1] Measured 3 mm from package.

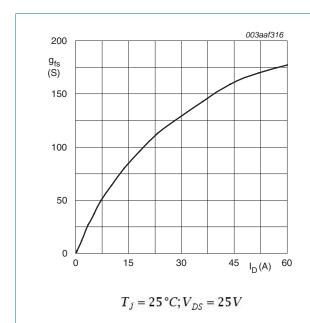


Fig 5. Forward transconductance as a function of drain current; typical values

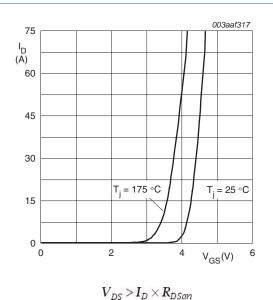


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

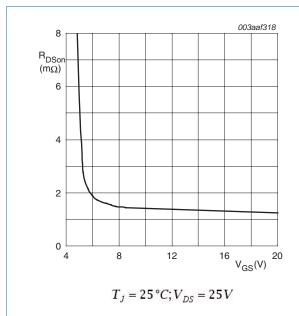


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values.

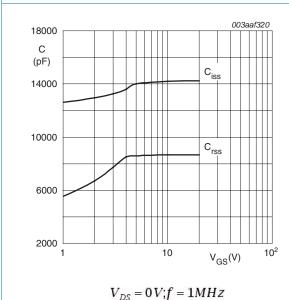
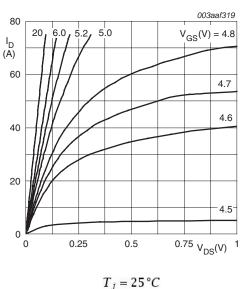
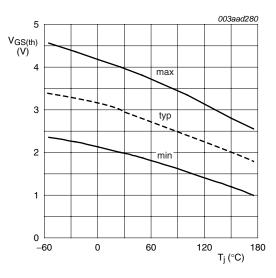


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



 $I_j = 25^{\circ}C$ 

Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$ 

Fig 10. Gate-source threshold voltage as a function of junction temperature

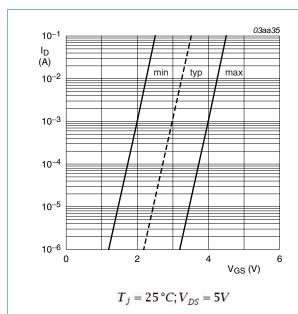


Fig 11. Sub-threshold drain current as a function of gate-source voltage

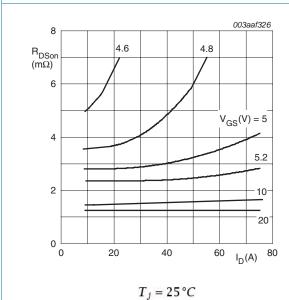


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

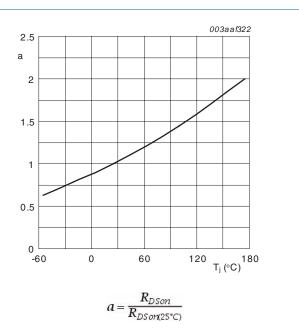


Fig 12. Normalized drain-source on state resistance factor as a function of junction temperature

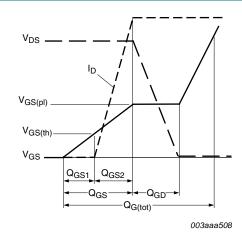


Fig 14. Gate charge waveform definitions

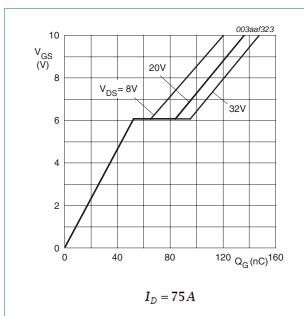
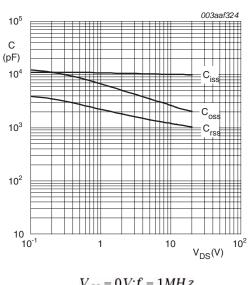


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

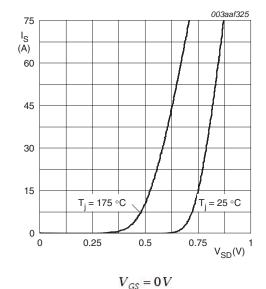


Fig 17. Source current as a function of source-drain voltage; typical values

### 7. Package outline

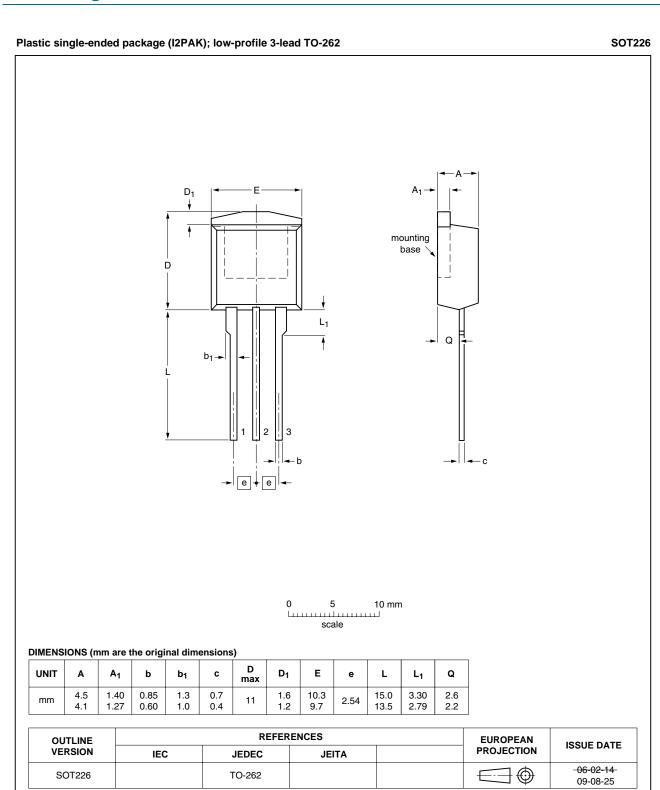


Fig 18. Package outline SOT226 (I2PAK)

### 8. Revision history

### Table 7. Revision history

| Document ID      | Release date | Data sheet status  | Change notice | Supersedes |
|------------------|--------------|--------------------|---------------|------------|
| PSMN1R5-40ES v.1 | 20110419     | Product data sheet | -             | -          |

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# **PSMN1R5-40ES**

### **Nexperia**

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